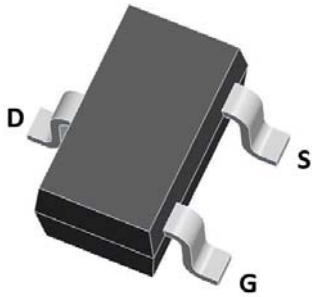
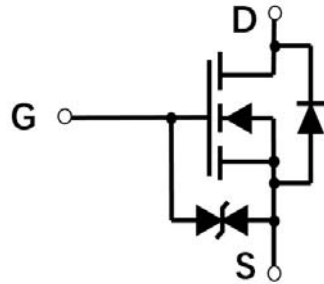
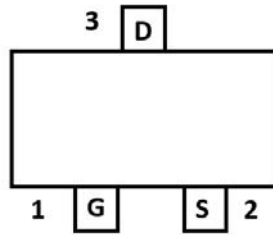


N-Channel Enhancement Mode Field Effect Transistor



SOT-323



Product Summary

- V_{DS} 60V
- I_D 300mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <2.5ohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <3.0ohm
- ESD Protected Up to 2.0KV (HBM)

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ\text{C}$ @ Steady State	300
		$T_A=70^\circ\text{C}$ @ Steady State	240
Pulsed Drain Current ^A	I_{DM}	1.5	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	300	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	416	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002KCWQ	F2	72KC.	3000	30000	120000	7" reel



2N7002KCWQ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D =300mA		1.9	2.5	Ω
		V _{GS} = 4.5V, I _D =200mA		2.0	3.0	
Diode Forward Voltage	V _{SD}	I _S =300mA, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				300	mA
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1MHZ		27		pF
Output Capacitance	C _{oss}			3		
Reverse Transfer Capacitance	C _{rss}			2		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =30V, I _D =0.3A		1.65	2.4	nC
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =30V, I _D =300mA, R _{GEN} =6Ω		6.5		ns
Turn-off Delay Time	t _{D(off)}			9.6		
Reverse recovery Time	t _{rr}	V _{GS} =0V, I _S =300mA, V _R =25V, di/dt=-100A/μs		24		ns

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

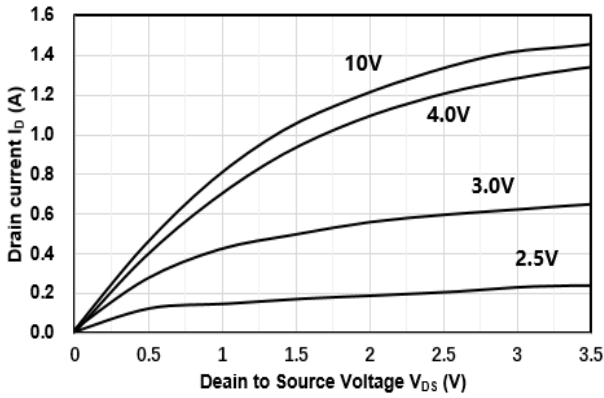


Figure1. Output Characteristics

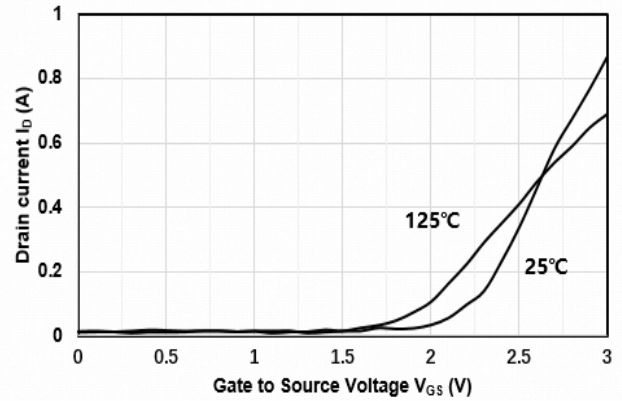


Figure2. Transfer Characteristics

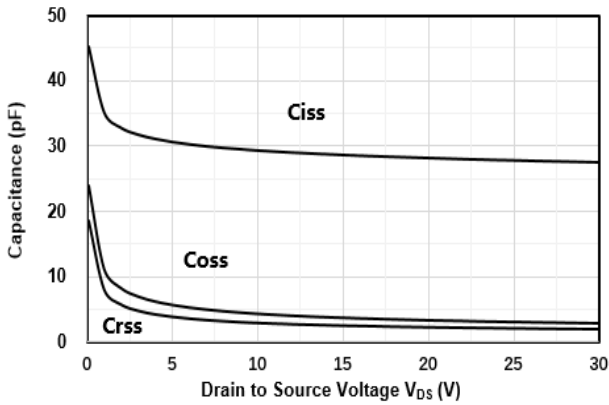


Figure3. Capacitance Characteristics

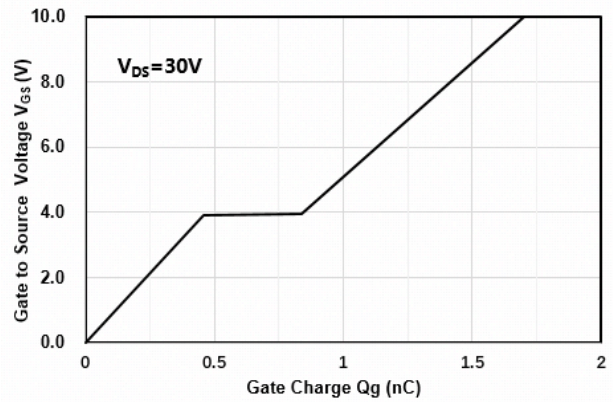


Figure4. Gate Charge

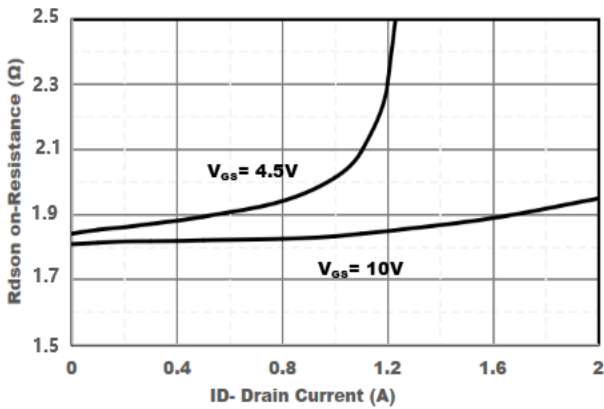


Figure5. Drain-Source on Resistance

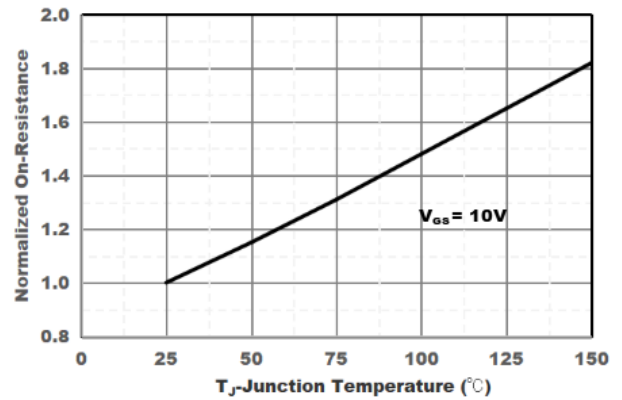


Figure6. Drain-Source on Resistance



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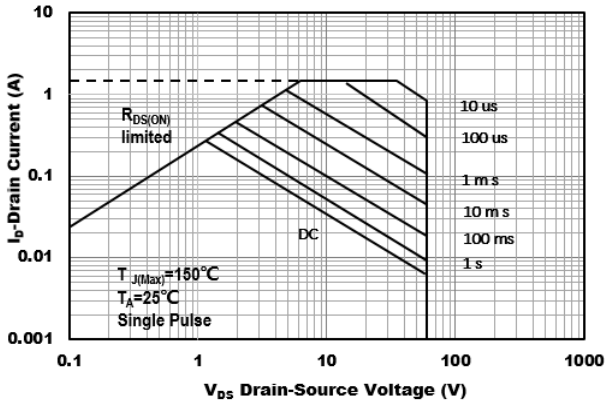


Figure7. Safe Operation Area

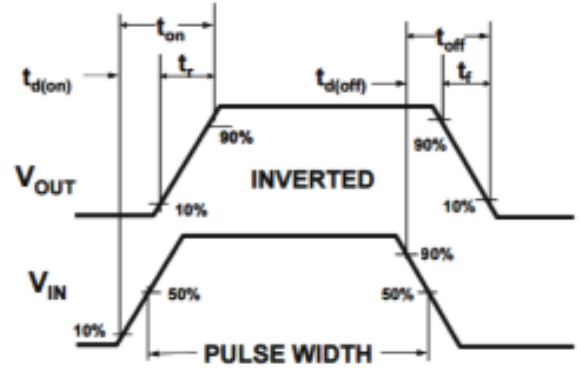
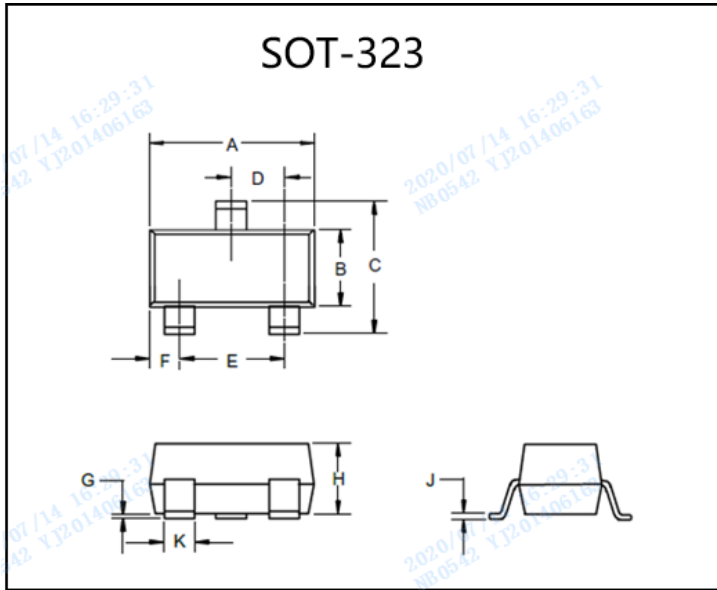


Figure8. Switching wave



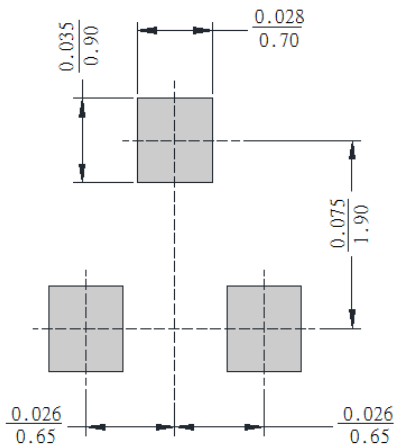
2N7002KCWQ

■SOT-323 Package Outline Dimensions



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.083	0.096	2.10	2.45	
D	0.026Nominal		0.65Nominal		
E	0.047	0.055	1.20	1.40	
F	0.012	0.016	0.30	0.40	
G	0.000	0.004	0.00	0.10	
H	0.035	0.039	0.90	1.00	
J	0.004	0.010	0.10	0.250	
K	0.006	0.016	0.15	0.40	

■SOT-323 Suggested Pad Layout





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2N7002KCWQ

REV.	EFFECTIVE DATE	REVISION HISTORY	PREPARED
1.0	2021.06.11	New release	Zhenzhong Zhao

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